

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74LCX08F, TC74LCX08FK

Low-Voltage Quad 2-Input AND Gate with 5-V Tolerant Inputs and Outputs

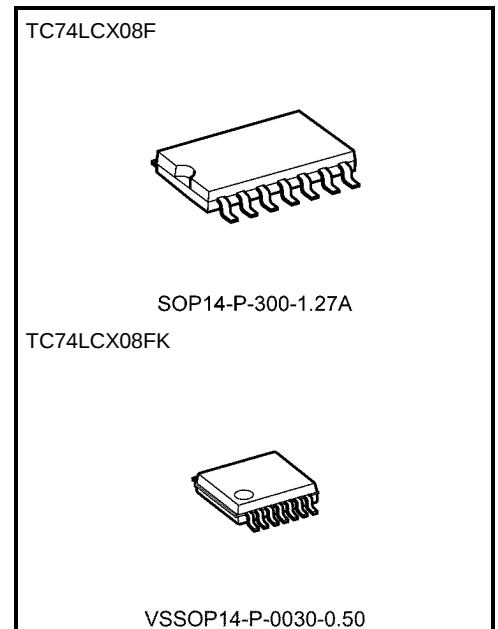
The TC74LCX08 is a high-performance CMOS 2-input AND gate. Designed for use in 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

The device is designed for low-voltage (3.3 V) V_{CC} applications, but it could be used to interface to 5-V supply environment for inputs.

All inputs are equipped with protection circuits against static discharge.

Features

- Low-voltage operation: $V_{CC} = 2.0$ to 3.6 V
- High-speed operation: $t_{pd} = 5.5$ ns (max) ($V_{CC} = 3.0$ to 3.6 V)
- Output current: $|I_{OH}|/I_{OL} = 24$ mA (min) ($V_{CC} = 3.0$ V)
- Available in JEITA SOP, VSSOP (US)
- Power-down protection provided on all inputs and outputs
- Pin and function compatible with the 74 series (74AC/VHC/HC/F/ALS/LS etc.) 08 type



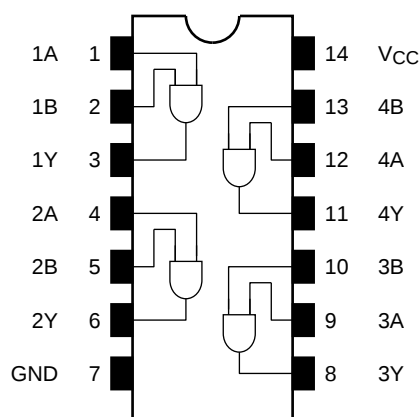
Weight

SOP14-P-300-1.27A : 0.18 g (typ.)

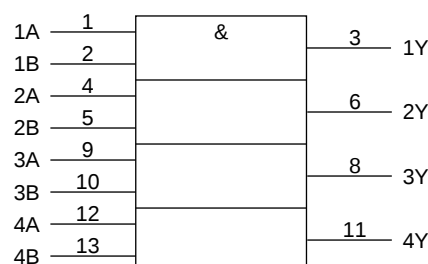
VSSOP14-P-0030-0.50 : 0.02 g (typ.)

Start of commercial production
1994-10

Pin Assignment (top view)



IEC Logic Symbol



Truth Table

Inputs		Outputs
A	B	Y
L	L	L
L	H	L
H	L	L
H	H	H

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	−0.5 to 7.0	V
DC input voltage	V _{IN}	−0.5 to 7.0	V
DC output voltage	V _{OUT}	−0.5 to 7.0 (Note 2)	V
		−0.5 to V _{CC} + 0.5 (Note 3)	
Input diode current	I _{IK}	−50	mA
Output diode current	I _{OK}	±50 (Note 4)	mA
DC output current	I _{OUT}	±50	mA
Power dissipation	P _D	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	−65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: V_{CC} = 0 V

Note 3: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 4: V_{OUT} < GND, V_{OUT} > V_{CC}

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Power Supply voltage	V _{CC}	2.0 to 3.6	V
		1.5 to 3.6 (Note 2)	
Input voltage	V _{IN}	0 to 5.5	V
Output voltage	V _{OUT}	0 to 5.5 (Note 3)	V
		0 to V _{CC} (Note 4)	
Output current	I _{OH} /I _{OL}	±24 (Note 5)	mA
		±12 (Note 6)	
Operating temperature	T _{opr}	−40 to 85	°C
Input rise and fall time	dt/dv	0 to 10 (Note 7)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.
Unused inputs must be tied to either V_{CC} or GND.

Note 2: Data retention only

Note 3: V_{CC} = 0 V

Note 4: High or low state

Note 5: V_{CC} = 3.0 to 3.6 V

Note 6: V_{CC} = 2.7 to 3.0 V

Note 7: V_{IN} = 0.8 to 2.0 V, V_{CC} = 3.0 V

Electrical Characteristics

DC Characteristics (T_a = −40 to 85°C)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	H-level	V _{IH}	—		2.7 to 3.6	2.0	—	V
	L-level	V _{IL}	—		2.7 to 3.6	—	0.8	
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH}	I _{OH} = −100 μA	2.7 to 3.6	V _{CC} − 0.2	—	V
				I _{OH} = −12 mA	2.7	2.2	—	
				I _{OH} = −18 mA	3.0	2.4	—	
				I _{OH} = −24 mA	3.0	2.2	—	
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7 to 3.6	—	0.2	
				I _{OL} = 12 mA	2.7	—	0.4	
				I _{OL} = 16 mA	3.0	—	0.4	
				I _{OL} = 24 mA	3.0	—	0.55	
Input leakage current		I _{IN}	V _{IN} = 0 to 5.5 V		2.7 to 3.6	—	±5.0	μA
Power-off leakage current		I _{OFF}	V _{IN} /V _{OUT} = 5.5 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		2.7 to 3.6	—	10.0	μA
			V _{IN} = 3.6 to 5.5 V		2.7 to 3.6	—	±10.0	
Increase in I _{CC} per input		ΔI _{CC}	V _{IH} = V _{CC} − 0.6 V (per 1 input)		2.7 to 3.6	—	500	

AC Characteristics (Ta = -40 to 85°C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
Propagation delay time	t _{pLH}	Figure 1, Figure 2	2.7	—	6.2	ns
	t _{pHL}		3.3 ± 0.3	1.5	5.5	
Output to output skew	t _{osLH}	(Note)	2.7	—	—	ns
	t _{osHL}		3.3 ± 0.3	—	1.0	

Note: Parameter guaranteed by design.
 (t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)

Dynamic Switching Characteristics (Ta = 25°C, input: tr = tf = 2.5 ns, CL = 50 pF, RL = 500 Ω)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V _{OL}	V _{OLP}	V _{IH} = 3.3 V, V _{IL} = 0 V	3.3	0.8	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	V _{IH} = 3.3 V, V _{IL} = 0 V	3.3	0.8	V

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Input capacitance	C _{IN}	—	3.3	7	pF
Output capacitance	C _{OUT}	—	0	8	pF
Power dissipation capacitance	CPD	f _{IN} = 10 MHz (Note)	3.3	25	pF

Note: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}(\text{opr}) = \text{CPD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 \text{ (per gate)}$$

AC Test Circuit

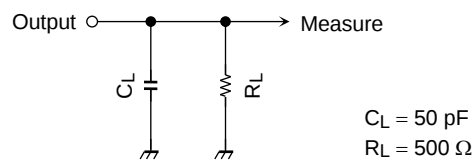


Figure 1

AC Waveform

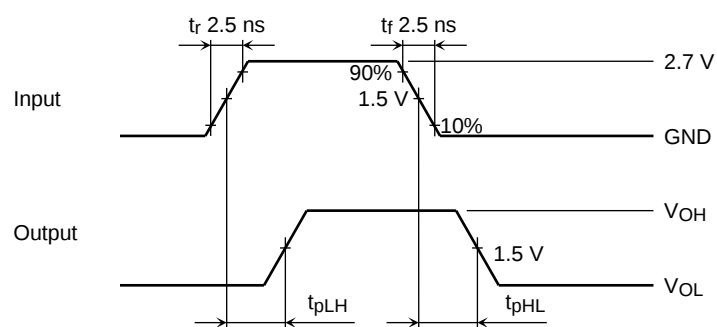
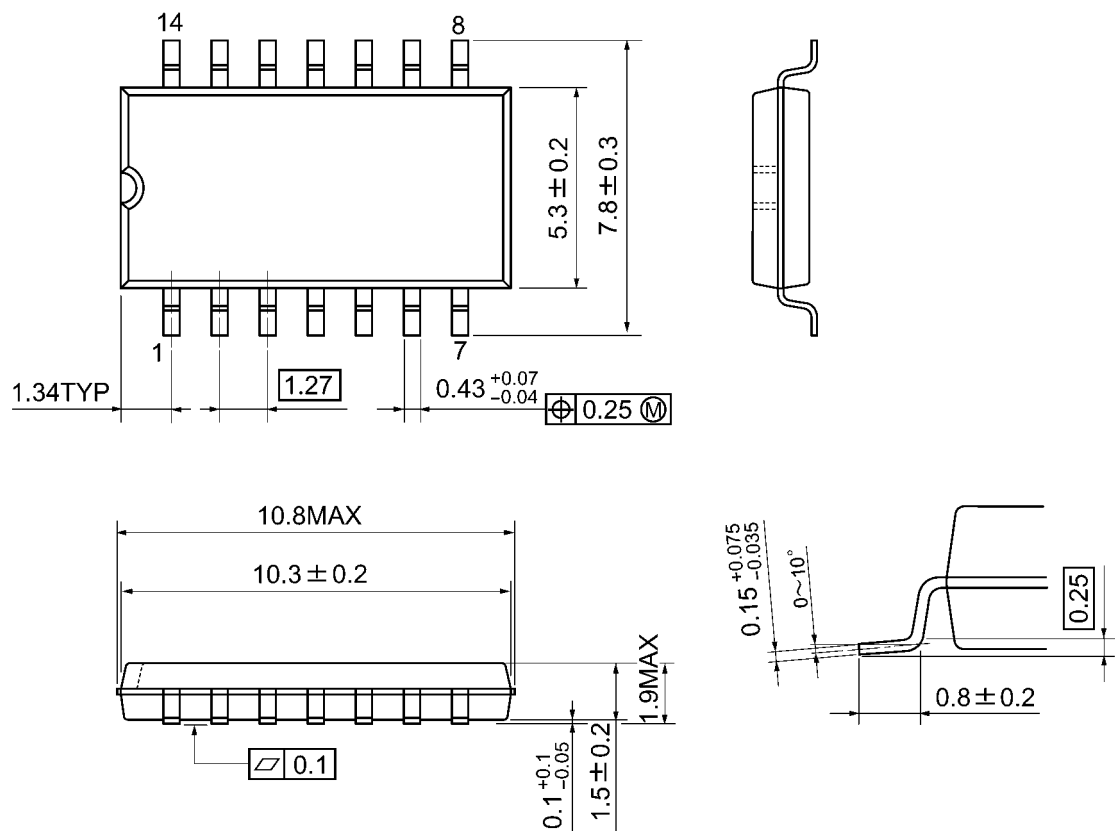


Figure 2 t_{pLH} , t_{pHL}

Package Dimensions

SOP14-P-300-1.27A

Unit: mm

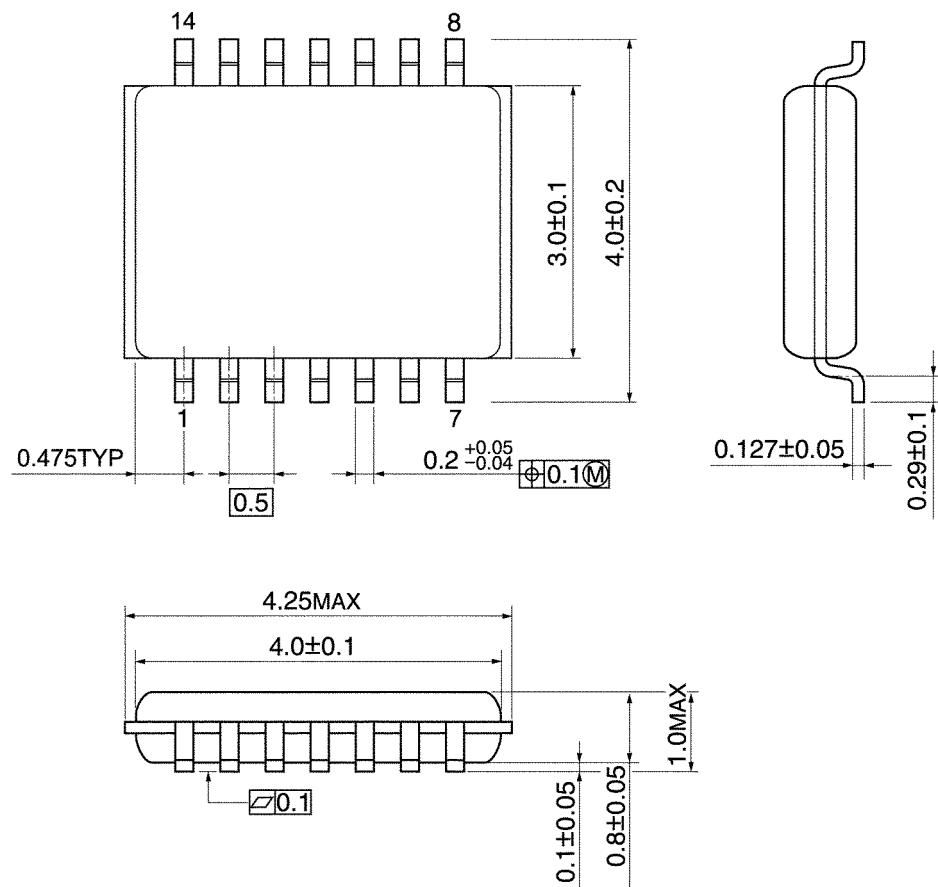


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Package Dimensions

VSSOP14-P-0030-0.50

Unit: mm



Weight: 0.02 g (typ.)